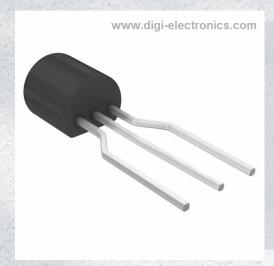


MPSA29_D75Z Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number MPSA29_D75Z-DG

Manufacturer onsemi

Manufacturer Product Number MPSA29_D75Z

Description TRANS NPN DARL 100V 0.8A T092-3

Detailed Description Bipolar (BJT) Transistor NPN - Darlington 100 V 800

mA 125MHz 625 mW Through Hole TO-92-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



MPSA29

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MPSA29_D75Z	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN - Darlington	800 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, Ic:
100 V	1.5V @ 100μA, 100mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
500nA	10000 @ 100mA, 5V
Power - Max:	Frequency - Transition:
625 mW	125MHz
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-226-3, TO-92-3 (TO-226AA) Formed Leads	TO-92-3
Base Product Number:	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
FAR99	8541.21.0075

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MPSA29 is a Preferred Device

Darlington Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector-Emitter Voltage	MPSA28 MPSA29	V _{CES}	80 100	Vdc
Collector-Base Voltage	ollector-Base Voltage MPSA28 MPSA29		80 100	Vdc
Emitter-Base Voltage		V _{EBO}	12	Vdc
Collector Current - Continuous		Ic	500	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C		P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C		P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range		T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

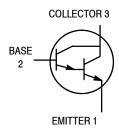
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

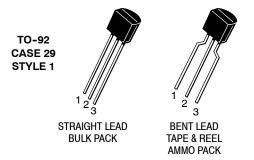
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



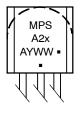
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MARKING DIAGRAM



= 8 or 9

= Assembly Location

= Year = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
MPSA28RLRPG	TO-92 (Pb-Free)	2000/Ammo Pack
MPSA29G	TO-92 (Pb-Free)	5000 Units/Bulk
MPSA29RLRP	TO-92	2000/Ammo Pack
MPSA29RLRPG	TO-92 (Pb-Free)	2000/Ammo Pack

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I _C = 100 μAdc, V _{BE} = 0)	MPSA28 MPSA29	V _{(BR)CES}	80 100	-		Vdc
Collector-Base Breakdown Voltage ($I_C = 100 \mu Adc, I_E = 0$)	MPSA28 MPSA29	V _{(BR)CBO}	80 100	-		Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)		V _{(BR)EBO}	12	-	-	Vdc
Collector Cutoff Current $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 80 \text{ Vdc}, I_E = 0)$	MPSA28 MPSA29	Ісво	-	-	100 100	nAdc
Collector Cutoff Current $(V_{CE} = 60 \text{ Vdc}, V_{BE} = 0)$ $(V_{CE} = 80 \text{ Vdc}, V_{BE} = 0)$	MPSA28 MPSA29	I _{CES}	-	-	500 500	nAdc
Emitter Cutoff Current (V _{EB} = 10 Vdc, I _C = 0)		I _{EBO}	-	-	100	nAdc
ON CHARACTERISTICS (Note 1)						
DC Current Gain ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 100 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)		h _{FE}	10,000 10,000	-		-
Collector-Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 0.01 \text{ mAdc}$) ($I_C = 100 \text{ mAdc}$, $I_B = 0.1 \text{ mAdc}$)		V _{CE(sat)}		0.7 0.8	1.2 1.5	Vdc
Base-Emitter On Voltage (I _C = 100 mAdc, V _{CE} = 5.0 Vdc)		V _{BE(on)}	-	1.4	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain - Bandwidth Product (Note 2) (I _C = 10 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)		fT	125	200	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		Cobo	-	5.0	8.0	pF

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%. 2. $f_T = h_{fe} \bullet f_{test}$.

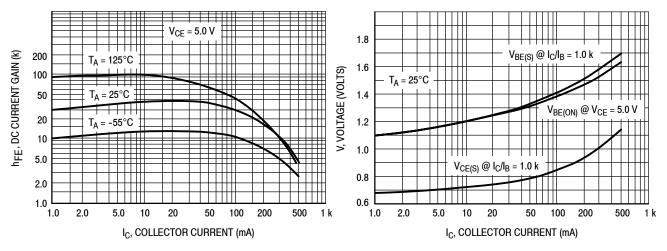


Figure 1. DC Current Gain

Figure 2. "ON" Voltages

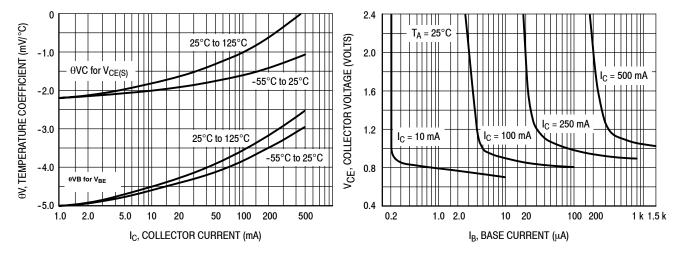


Figure 3. Temperature Coefficients

Figure 4. Collector Saturation Region

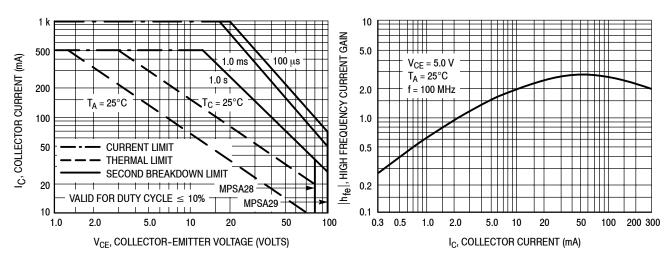
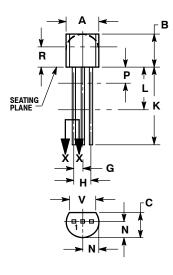


Figure 5. Active Region - Safe Operating Area

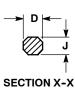
Figure 6. High Frequency Current Gain

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



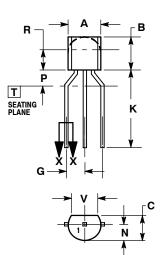
STRAIGHT LEAD **BULK PACK**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
- IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
ν	0 135		3 43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
 DIMENSION R IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P
- AND BEYOND DIMENSION K MINIMUM

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
V	3.43		

STYLE 1: PIN 1. EMITTER

BASE

COLLECTOR

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